



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-06C Plastic-Encapsulate Diodes

FBAT54CDW

SURFACE MOUNT SCHOTTKY BARRIER DIODE ARRAYS

DESCRIPTION

Silicon epitaxial planar

PN Junction Guard Ring for Schottky Diode

FEATURES

- Low Forward Voltage Drop
- Fast Switching SCHOTTKY DIODE

APPLICATION

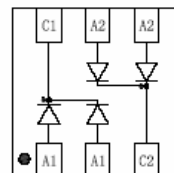
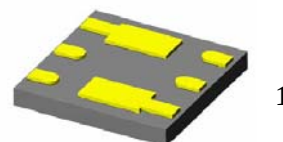
Ultra high speed switching, rectifiers

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

WBFBP-06C

(2×2×0.5)

unit: mm



FBAT54CDW

Marking:KL7

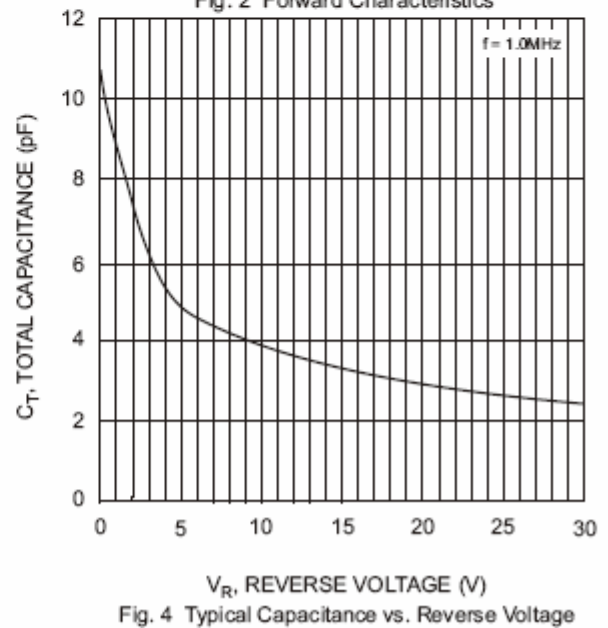
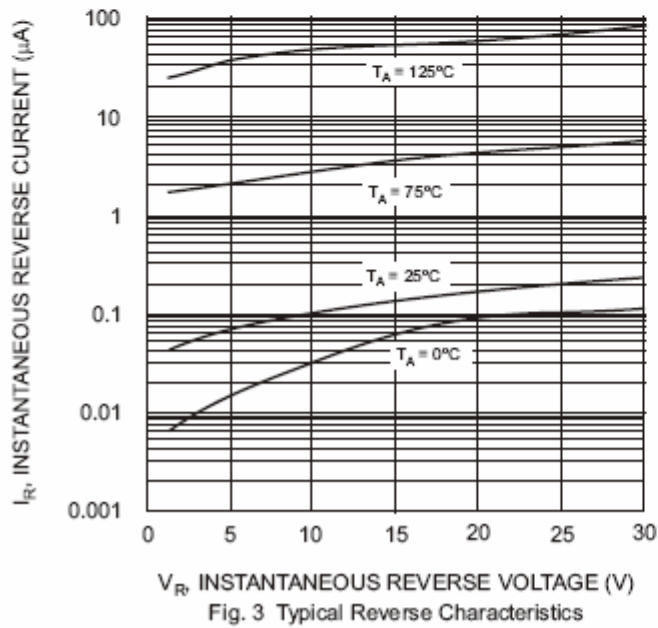
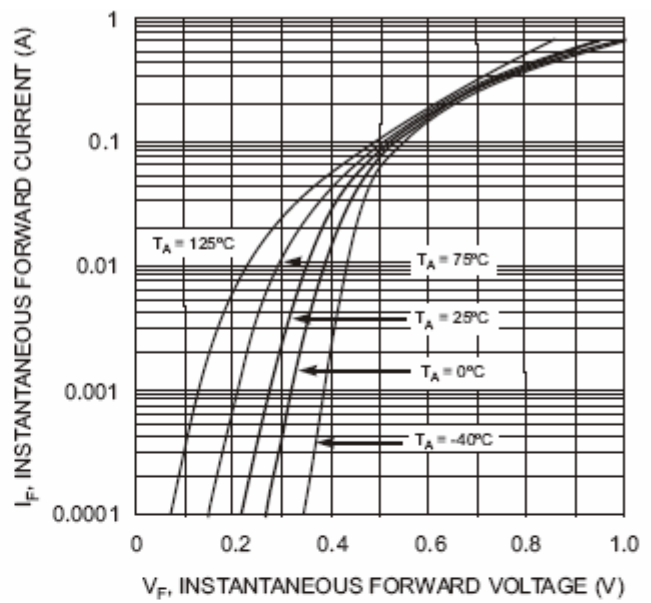
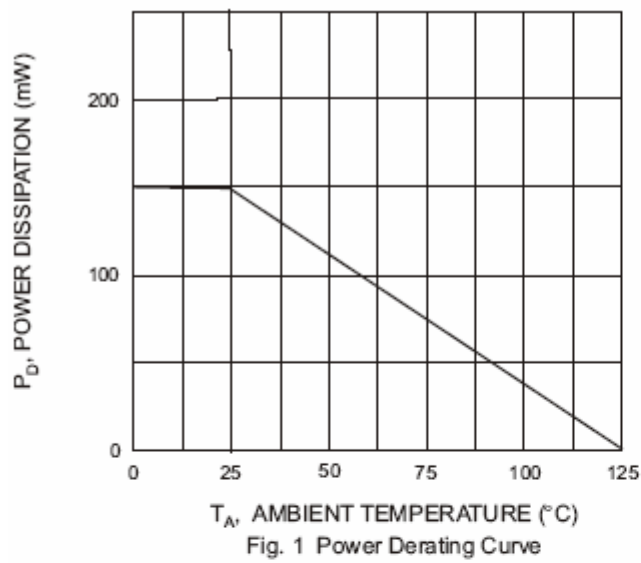
Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak Repetitive reverse voltage DC Blocking Voltage	V_{RM} V_R	30	V
Average Rectified Output Current	I_O	100	mA
Power Dissipation	P_D	150	mW
Junction temperature	T_J	125	°C
Storage temperature range	T_{STG}	-65-125	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

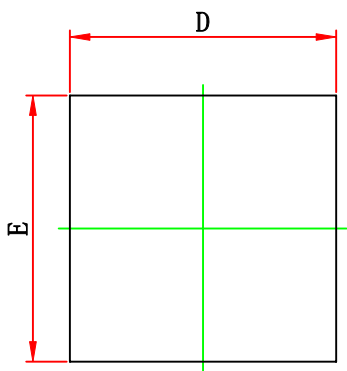
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100 \mu A$	30		V
Reverse voltage leakage current	I_R	$V_R = 25V$		2	μA
Forward voltage	V_F	$I_F = 0.1mA$ $I_F = 1mA$ $I_F = 10mA$ $I_F = 30mA$ $I_F = 100mA$		240 320 400 500 1000	mV
Total capacitance	C_T	$V_R = 1V, f = 1MHz$		10	pF
Reverse recovery time	t_{rr}	$I_F = 10mA, I_R = 10mA \sim 1mA$ $R_L = 100 \Omega$		5	nS

Typical Characteristics

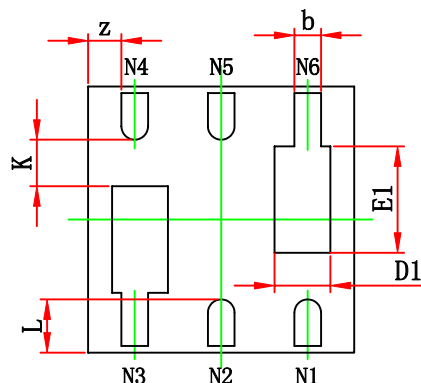




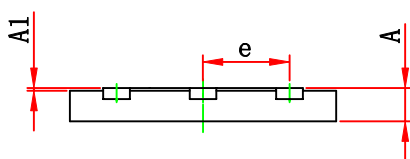
WBFBP-06C(2×2×0.5) PACKAGE OUTLINE DIMENSIONS



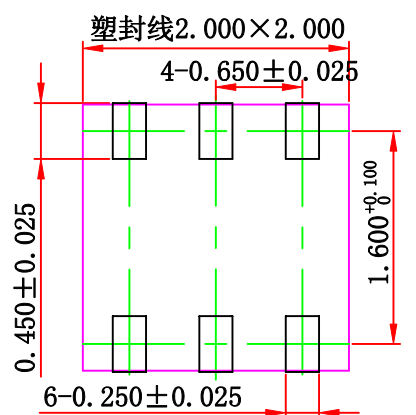
TOP VIEW



BOTTOM VIEW



SIDE VIEW

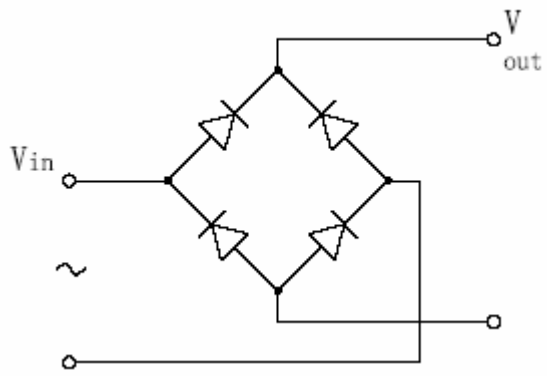


LAND PATTERN RECOMMENDATION

推荐焊盘图

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.000	0.100	0.000	0.004
b	0.150	0.250	0.006	0.010
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.420 REF.		0.017 REF.	
E1	0.800 REF.		0.032 REF.	
e	0.650 TYP.		0.026 TYP.	
L	0.400 REF.		0.016 REF.	
k	0.350 REF.		0.014 REF.	
z	0.500 REF.		0.020 REF.	

APPLICATION CIRCUITS



Bridge rectifiers